

CMKSH-3DO
ULTRAmi™
DUAL OPPOSING
SCHOTTKY DIODES

Central™
Semiconductor Corp.

FEATURES:

- DUAL OPPOSING (DO) SCHOTTKY DIODES
- SPACE SAVINGS ULTRAmi™ FAMILY
- GALVANICALLY ISOLATED
- LOW FORWARD VOLTAGE
(0.58V TYP @ 100mA)

ULTRAmi™



SOT-363 CASE

DESCRIPTION:

The Central Semiconductor CMKSH-3DO incorporates two galvanically isolated, Low V_F Silicon Diodes with an opposing Anode/Cathode configuration, in a space saving surface mount package, designed for fast switching applications requiring a low forward voltage drop. Marking code is **KDO**.

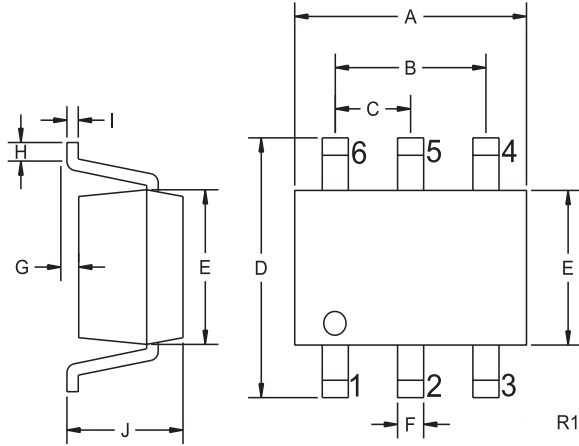
MAXIMUM RATINGS: ($T_A=25^\circ\text{C}$)

	<u>SYMBOL</u>		<u>UNITS</u>
Peak Repetitive Reverse Voltage	V_{RRM}	30	V
Continuous Forward Current	I_F	100	mA
Forward Power Dissipation	P_D	250	mW
Operating and Storage			
Junction Temperature	T_J, T_{stg}	-65 to +150	$^\circ\text{C}$
Thermal Resistance	θ_{JA}	500	$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS PER DIODE: ($T_A=25^\circ\text{C}$ unless otherwise noted)

<u>SYMBOL</u>	<u>TEST CONDITIONS</u>	<u>MIN</u>	<u>TYP</u>	<u>MAX</u>	<u>UNITS</u>
I_R	$V_R=25\text{V}$			500	nA
I_R	$V_R=25\text{V}, T_A = 100^\circ\text{C}$			100	μA
BV_R	$I_R=100\mu\text{A}$	30			V
V_F	$I_F=2.0\text{mA}$			0.33	V
V_F	$I_F=15\text{mA}$			0.45	V
V_F	$I_F=100\text{mA}$		0.58	1.00	V
C_T	$V_R=1.0\text{V}, f=1.0\text{MHz}$		7.0		pF
t_{rr}	$I_F=I_R=10\text{mA}; I_{rr}=1.0\text{mA}, R_L=100\Omega$			5.0	ns

SOT-363 CASE - MECHANICAL OUTLINE

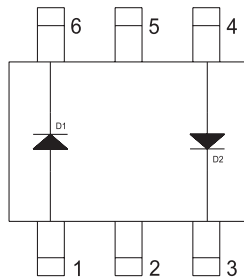


SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.073	0.085	1.85	2.15
B	0.051		1.30	
C	0.026		0.65	
D	0.075	0.091	1.90	2.30
E	0.043	0.055	1.10	1.40
F	0.006	0.012	0.15	0.30
G	0.000	0.004	0.00	0.10
H	0.010	-	0.25	-
I	0.004	0.010	0.10	0.25
J	0.031	0.039	0.80	1.00

SOT-363 (REV: R1)

MARKING CODE: KDO

Dual Opposing Configuration



LEAD CODE:

- 1) Anode D1
- 2) NC
- 3) Cathode D2
- 4) Anode D2
- 5) NC
- 6) Cathode D1

R0 (10-December 2001)